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## Correction: Facile synthesis of silicon quantum dots with photoluminescence in the near-ultraviolet to violet region *via* wet oxidation

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Correction for 'Facile synthesis of silicon quantum dots with photoluminescence in the near-ultraviolet to violet region *via* wet oxidation' by Yizhou He *et al.*, *J. Mater. Chem. C*, 2024, <https://doi.org/10.1039/d4tc02095b>.

The authors regret errors in Fig. 1 of the published article: "1. Thermal pyrolysis under argon" should read "1. Hydrolysis–condensation under argon"; in addition, "PH = 3" should read "pH = 3". In Fig. 9 "(2) Nonrecombination by Dangling Bonds" should read "(2) Nonradiative Recombination by Dangling Bonds". These errors do not impact any of the conclusions of the article. The corrected versions of Fig. 1 and Fig. 9 are shown here:

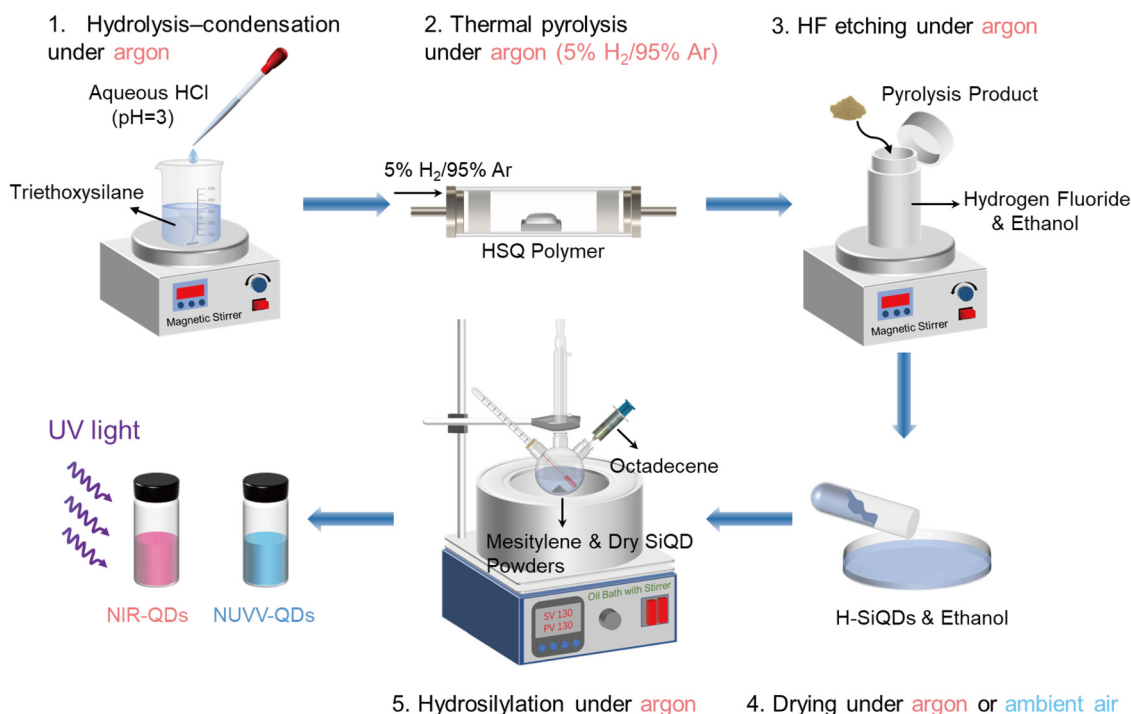


Fig. 1 A schematic diagram of the synthesis routes for NIR-emitting and NUVV-emitting SiQDs.

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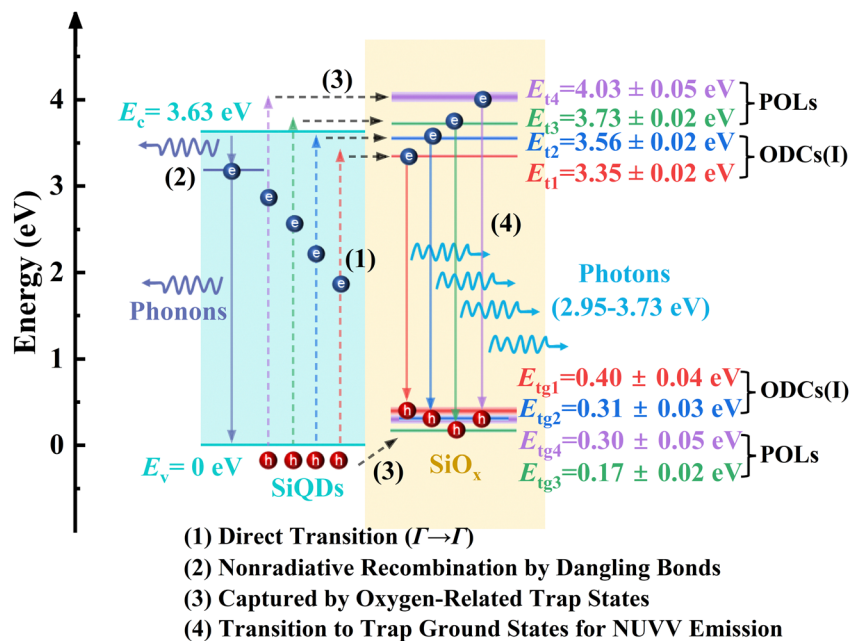


Fig. 9 A schematic diagram of the emission mechanisms of NUVV-QDs.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

